

UNITED STATES PATENT AND TRADEMARK OFFICE
CERTIFICATE OF CORRECTION

PATENT NO. : 6,961,277 B2
DATED : November 1, 2005
INVENTOR(S) : John T. Moore et al.

Page 1 of 3

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

Title page.

Item [56], **References Cited**, U.S. PATENT DOCUMENTS, add:

-- 3,622,319	11/1971	Sharp
3,743,847	7/1973	Boland
4,269,935	5/1981	Masters et al.
4,312,938	1/1982	Drexler, et al.
4,316,946	1/1982	Masters, et al.
4,320,191	3/1982	Yoshikawa et al.
4,405,710	9/1983	Balasubramanyam et al.
4,419,421	12/1983	Wichelhaus, et al.
4,499,557	2/1985	Holmberg et al.
4,671,618	06/09/1987	Wu et al.
4,795,657	1/1989	Formigoni et al.
4,800,526	01/24/1989	Lewis
4,847,674	7/1989	Sliwa et al.
5,219,788	6/1993	Abernathey et al.
5,238,862	8/1993	Blalock et al.
5,272,359	12/21/1993	Nagasubramanian et al.
5,314,772	5/24/1994	Kozicki
5,315,131	5/1994	Kishimoto et al.
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5,360,981	11/1994	Owen et al.
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5,512,773	4/1996	Wolf et al.
5,726,083	3/1998	Takaishi
5,751,012	5/12/1998	Wolstenholme et al.
5,761,115	6/1998	Kozicki et al.
5,789,277	8/1998	Zahorik et al.
5,814,527	9/29/1998	Wolstenholme et al.
5,818,749	10/06/1998	Harshfield
5,841,150	11/1998	Gonzalez et al.
5,846,889	12/1998	Harbison et al.
5,851,882	12/22/1998	Harshfield
5,869,843	2/9/1999	Harshfield
5,896,312	4/20/1999	Kozicki et al.
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5,920,788	7/1999	Reinberg
5,998,066	12/1999	Block et al.
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Title page (cont'd).

6,077,729	6/2000	Harshfield
6,084,769	7/4/2000	Kozicki et al.
6,177,338	1/2001	Liaw et al.
6,117,720	9/2000	Harshfield
6,143,604	11/2000	Chiang et al.
6,236,059	5/2001	Wolstenholme et al.
6,297,170	10/2001	Gabriel et al.
6,300,684	10/2001	Gonzalez et al.
6,316,684	11/2001	Zahorik et al.
6,511,867	1/2003	Lowery et al. --;

OTHER PUBLICATIONS,

"Bondarev, V.N.; Pikhitsa, P.V., A dendrite model of current instability in RgAg₄I₅. Solid State Ionics 70/71 (1994) 72-76." should read

-- Bondarev, V.N.; Pikhitsa, P.V., A dendrite model of current instability in RbAg₄I₅. Solid State Ionics 70/71 (1994) 72-76. --;

"Cahen, D.; Gilet, J.-M.; Schmitz, C.; Chernyak, L.; Gartsman, K.; Jakubowicz, A., Room-Temperature electric field induced creation of stable devices in CuInSe₂ Crystals, Science 258 (1992) 271-271." should read

-- Cahen, D.; Gilet, J.-M.; Schmitz, C.; Chernyak, L.; Gartsman, K.; Jakubowicz, A., Room-Temperature electric field induced creation of stable devices in CuInSe₂ Crystals, Science 258 (1992) 271-271. --;

"El Bouchairi, B.; Bernede, J.C.; Burgaud, P., Properties of Ag_{2-x}Se_{1+x}/n-Si diodes, Thin Solid Films 110 (1983) 107-113." should read

-- El Bouchairi, B.; Bernede, J.C.; Burgaud, P., Properties of Ag_{2-x}Se_{1+x}/n-Si diodes, Thin Solid Films 110 (1983) 107-113. --;

"West, W.C.; Sieradzki, K.; Kardynal, B.; Kozicki, M.N., Equivalent circuit modeling of the AgIAs_{0.24}S_{0.36}Ag_{0.40}IAg systems prepared by photodissolution of Ag, J. Electrochem. Soc. 145 (1998) 2971-2974." should read

-- West, W.C.; Sieradzki, K.; Kardynal, B.; Kozicki, M.N., Equivalent circuit modeling of the AgIAs_{0.24}S_{0.36}Ag_{0.40}IAg systems prepared by photodissolution of Ag, J. Electrochem. Soc. 145 (1998) 2971-2974. --.

"Kotkata, M.F.; Afif, M.A.; Labib, H.H.; Hegab, N.A.; Abdel-Aziz, M.M., Memory switching in amorphous GeSeTe chalcogenide semiconductor films, Thin Solid Films 240 (1994) 143-146." should read

-- Kotkata, M.F.; Afifi, M.A.; Labib, H.H.; Hegab, N.A.; Abdel-Aziz, M.M., Memory switching in amorphous GeSeTe chalcogenide semiconductor films, Thin Solid Films 240 (1994) 143-146. --;

"McHardy et al., The dissolution of metals in amorphous chalcogenides and the effects of electron and ultraviolet radiation, 20 J. Phys. C.: Solid State Phys., pp. 4055-4075 (1987)f." should read

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Title page (cont'd).

-- McHardy et al., The dissolution of metals in amorphous chalcogenides and the effects of electron and ultraviolet radiation, 20 J. Phys. C.: Solid State Phys., pp. 4055-4075 (1987). --;

"Rose, M.J.; Snell, A.J.; Lecomber, P.G.; Hajto, J.; Fitzgerald, A.G.; Owen, A.E., Aspects of non-volatility in a-Si:H memory devices, Mat. Res. Soc. Symp. Proc. V 258, 1992, 1075-1080." should read

-- Rose, M.J.; Snell, A.J.; Lecomber, P.G.; Hajto, J.; Fitzgerald, A.G.; Owen, A.E., Aspects of non-volatility in metal/a -Si:H/metal memory devices, Mat. Res. Soc. Symp. Proc. V 258, 1992, 1075-1080. --; and

"Tranchant, S.; Peytavin, S.; Ribes, M.; Flank, A.M.; Despert, H.; Lagarde, J.P., Silver chalcogenide glasses Ag-Ge-Se: Ionic conduction and exafs structural investigation, Transport-structure relations in fast ion and mixed conductors Proceedings of the 6th Riso International symposium, Sep. 9-13, 1985." should read

-- Tranchant, S.; Peytavin, S.; Ribes, M.; Flank, A.M.; Despert, H.; Lagarde, J.P., Silver chalcogenide glasses Ag-Ge-Se: Ionic conduction and EXAFS structural investigation, Transport-structure relations in fast ion and mixed conductors, Proceedings of the 6th RISO International symposium, Sep. 9-13, 1985. --.

Column 11,

Line 6, "900 include" should read -- 900 includes --; and

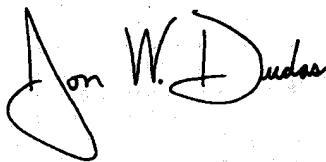
Line 56, "system" should read -- systems --.

Column 13,

Line 33, "a erase" should read -- an erase --.

Signed and Sealed this

Thirtieth Day of May, 2006



JON W. DUDAS

Director of the United States Patent and Trademark Office